

DATA SHEET

74F189A

64-bit TTL bipolar RAM, inverting
(3-State)

Product specification

1990 Feb 23

IC15 Data Handbook

64-bit TTL bipolar RAM, inverting (3-State)

74F189A

FEATURES

- High speed performance
- Replaces 74F189
- Address access time: 8ns max vs 28ns for 74F189
- Power dissipation: 4.3mW/bit
- Schottky clamp TTL
- One chip enable
- Inverting outputs (for non-inverting outputs see 74F219A)
- 3-State outputs
- 74F189A in 150 mil wide SO is preferred options for new designs

are fully decoded on chip. The outputs are in high impedance state whenever the chip enable ($\overline{CE}$) is high. The outputs are active only in the READ mode ($\overline{WE}$ = high) and the output data is the complement of the stored data.

TYPE	TYPICAL ACCESS TIME	TYPICAL SUPPLY CURRENT (TOTAL)
74F189A	5.0ns	55mA

DESCRIPTION

The 74F189A is a high speed, 64-bit RAM organized as a 16-word by 4-bit array. Address inputs are buffered to minimize loading and

ORDERING INFORMATION

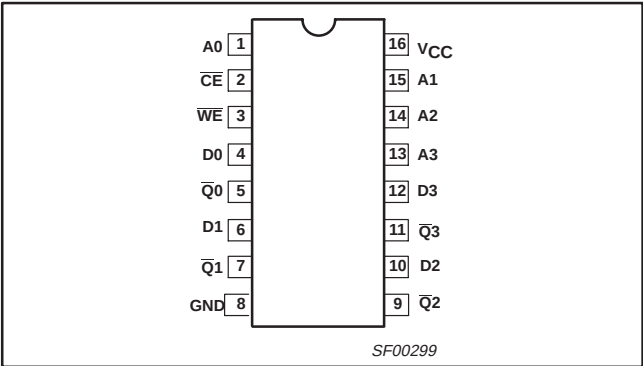
DESCRIPTION	ORDER CODE	DRAWING NUMBER
	COMMERCIAL RANGE $V_{CC} = 5V \pm 10\%$, $T_{amb} = 0^{\circ}C$ to $+70^{\circ}C$	
16-pin plastic Dual In-line Package	N74F189AN	SOT38-4
16-pin plastic Small Outline (150mil)	N74F189AD	SOT109-1

INPUT AND OUTPUT LOADING AND FAN OUT TABLE

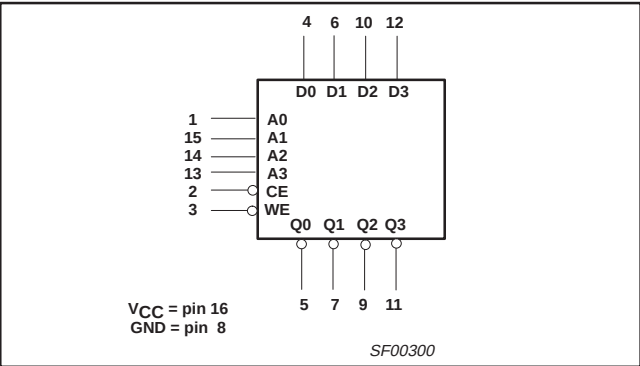
PINS	DESCRIPTION	74F (U.L.) HIGH/LOW	LOAD VALUE HIGH/LOW
D0 – D3	Data inputs	1.0/1.0	20 μ A/0.6mA
A0 – A3	Address inputs	1.0/1.0	20 μ A/0.6mA
$\overline{CE}$	Chip enable input (active low)	1.0/2.0	20 μ A/1.2mA
$\overline{WE}$	Write enable input (active low)	1.0/2.0	20 μ A/1.2mA
$\overline{Q0} - \overline{Q3}$	Data outputs	150/40	3mA/24mA

NOTE: One (1.0) FAST unit load is defined as: 20 μ A in the high state and 0.6mA in the low state.

PIN CONFIGURATION



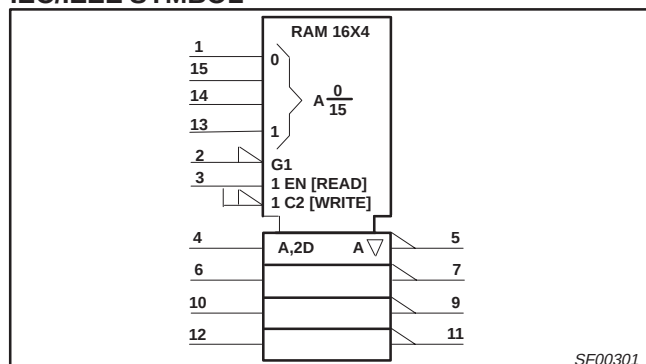
LOGIC SYMBOL



64-bit TTL bipolar RAM, inverting (3-State)

74F189A

IEC/IEEE SYMBOL



FUNCTION TABLE

INPUTS			OUTPUT	OPERATING MODE
CE	WE	Dn	$\overline{Q}_n$	
L	H	X	Complement of stored data	Read
L	L	L	High impedance	Write "0"
H	L	H	High impedance	Write "1"
H	X	X	High impedance	Disable input

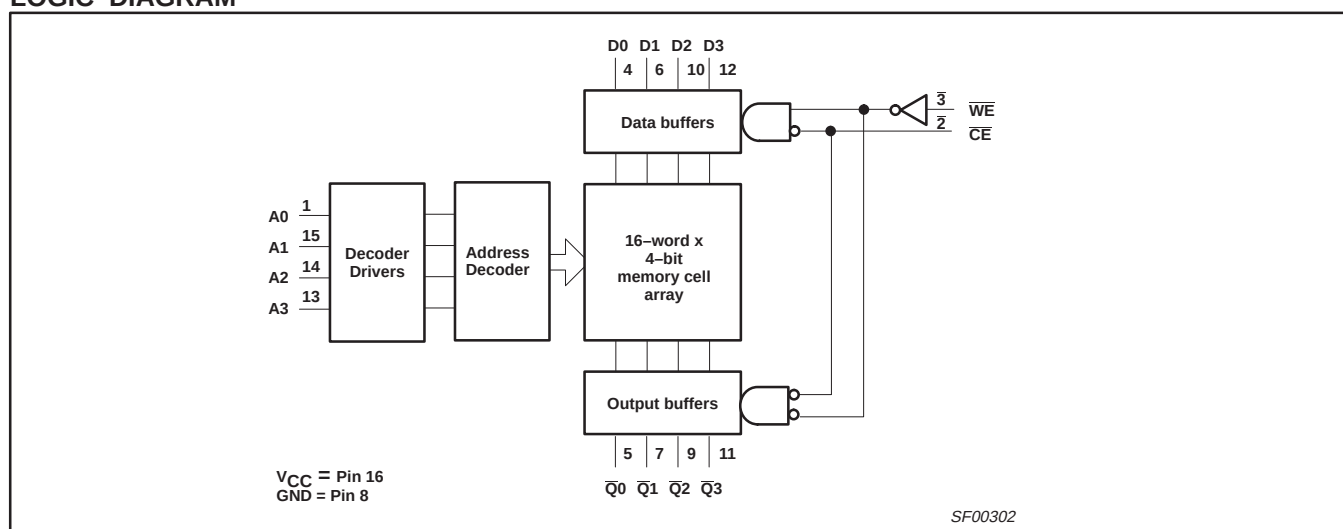
NOTES:

H = High voltage level

L = Low voltage level

X = Don't care

LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

(Operation beyond the limit set forth in this table may impair the useful life of the device. Unless otherwise noted these limits are over the operating free air temperature range.)

SYMBOL	PARAMETER	RATING	UNIT
V _{CC}	Supply voltage	−0.5 to +7.0	V
V _{IN}	Input voltage	−0.5 to +7.0	V
I _{IN}	Input current	−30 to +5	mA
V _{OUT}	Voltage applied to output in high output state	−0.5 to V _{CC}	V
I _{OUT}	Current applied to output in low output state	48	mA
T _{amb}	Operating free air temperature range	0 to +70	°C
T _{stg}	Storage temperature range	−65 to +150	°C

64-bit TTL bipolar RAM, inverting (3-State)

74F189A

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIMITS			UNIT
		MIN	NOM	MAX	
V_{CC}	Supply voltage	4.5	5.0	5.5	V
V_{IH}	High-level input voltage	2.0			V
V_{IL}	Low-level input voltage			0.8	V
I_{IK}	Input clamp current			-18	mA
I_{OH}	High-level output current			-3	mA
I_{OL}	Low-level output current			24	mA
T_{amb}	Operating free air temperature range	0		+70	°C

DC ELECTRICAL CHARACTERISTICS

(Over recommended operating free-air temperature range unless otherwise noted.)

over recommended operating free air temperature range unless otherwise noted.

SYMBOL	PARAMETER		TEST CONDITIONS ¹	LIMITS			UNIT
				MIN	TYP ²	MAX	
V _{OH}	High-level output voltage		V _{CC} = MIN, V _{IL} = MAX	±10%V _{CC}	2.4		V
			V _{IH} = MIN, I _{OH} = MAX	±5%V _{CC}	2.7	3.4	V
V _{OL}	Low-level output voltage		V _{CC} = MIN, V _{IL} = MAX	±10%V _{CC}		0.35	0.50
			V _{IH} = MIN, I _{OL} = MAX	±5%V _{CC}		0.35	0.50
V _{IK}	Input clamp voltage		V _{CC} = MIN, I _I = I _{IK}		-0.73	-1.2	V
I _I	Input current at maximum input voltage		V _{CC} = MAX, V _I = 7.0V			100	μA
I _{IH}	High-level input current		V _{CC} = MAX, V _I = 2.7V			20	μA
I _{IL}	Low-level input current	others	V _{CC} = MAX, V _I = 0.5V			-0.6	mA
		CE, WE				-1.2	mA
I _{OZH}	Offset output current, high-level voltage applied		V _{CC} = MAX, V _I = 2.7V			50	μA
I _{OZL}	Offset output current, low-level voltage applied		V _{CC} = MAX, V _I = 0.5V			-50	μA
I _{OS}	Short-circuit output current ³		V _{CC} = MAX	-60		-150	mA
I _{CC}	Supply current (total)		V _{CC} = MAX, CE = WE = GND		55	80	mA
C _{IN}	Input capacitance		V _{CC} = 5V, V _{IN} = 2.0V		4		pF
C _{OUT}	Output capacitance		V _{CC} = 5V, V _{OUT} = 2.0V		7		pF

NOTES:

- For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions for the applicable type.
- All typical values are at $V_{CC} = 5\text{V}$, $T_{amb} = 25^\circ\text{C}$.
- Not more than one output should be shorted at a time. For testing I_{OS} , the use of high-speed test apparatus and/or sample-and-hold techniques are preferable in order to minimize internal heating and more accurately reflect operational values. Otherwise, prolonged shorting of a high output may raise the chip temperature well above normal and thereby cause invalid readings in other parameter tests. In any sequence of parameter tests, I_{OS} tests should be performed last.

64-bit TTL bipolar RAM, inverting (3-State)

74F189A

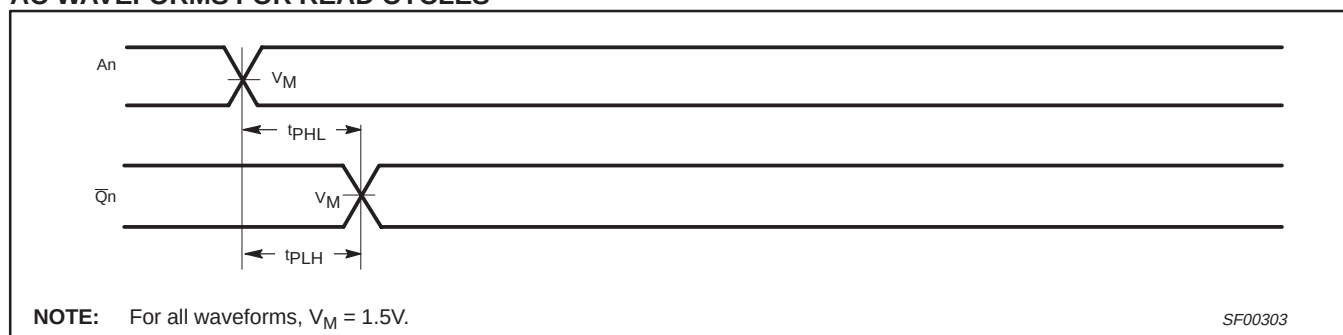
AC ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER		TEST CONDITION	LIMITS					UNIT
				T _{amb} = +25°C V _{CC} = +5.0V C _L = 50pF, R _L = 500Ω			T _{amb} = 0°C to +70°C V _{CC} = +5.0V ± 10% C _L = 50pF, R _L = 500Ω		
				MIN	TYP	MAX	MIN	MAX	
				MIN	TYP	MAX	MIN	MAX	
t _{PLH} t _{PHL}	Access time	Propagation delay An to Q̄n	Waveform 1	2.5 2.0	5.0 4.5	8.0 8.0	2.5 2.0	8.0 8.0	ns
t _{PZH} t _{PZL}		Enable time CE to Q̄n	Waveform 2	2.0 2.0	3.5 4.0	6.0 7.0	1.5 2.0	7.0 7.5	ns
t _{PHZ} t _{PLZ}	Disable time CE to Q̄n		Waveform 3	2.5 1.5	4.5 3.0	7.0 5.5	2.0 1.5	8.0 6.0	ns
t _{PZH} t _{PZL}	Write recovery time	Enable time WE to Q̄n	Waveform 4	2.0 2.5	4.0 4.5	6.5 7.5	2.0 2.5	7.0 8.0	ns
t _{PHZ} t _{PLZ}	Disable time WE to Q̄n		Waveform 4	3.5 1.5	5.5 3.5	8.5 6.5	3.0 1.5	9.0 7.0	ns

AC SETUP REQUIREMENT

SYMBOL	PARAMETER	TEST CONDITION	LIMITS					UNIT
			T _{amb} = +25°C V _{CC} = +5.0V C _L = 50pF, R _L = 500Ω			T _{amb} = 0°C to +70°C V _{CC} = +5.0V ± 10% C _L = 50pF, R _L = 500Ω		
			MIN	TYP	MAX	MIN	MAX	
t _{su} (H) t _{su} (L)	Setup time, high or low An to $\overline{WE}$	Waveform 4	4.5 4.5			5.0 5.0		ns
t _h (H) t _h (L)	Hold time, high or low An to $\overline{WE}$	Waveform 4	0 0			0 0		ns
t _{su} (H) t _{su} (L)	Setup time, high or low Dn to $\overline{WE}$	Waveform 4	7.5 6.5			9.0 8.0		ns
t _h (H) t _h (L)	Hold time, high or low Dn to $\overline{WE}$	Waveform 4	0 0			0 0		ns
t _{su} (L)	Setup time, low CE (falling edge) to $\overline{WE}$ (falling edge)	Waveform 4	0			0		ns
t _h (L)	Hold time, low $\overline{WE}$ (falling edge) to $\overline{WE}$ (rising edge)	Waveform 4	6.5			7.5		ns
t _w (L)	Pulse width, low $\overline{WE}$	Waveform 4	7.0			8.0		ns

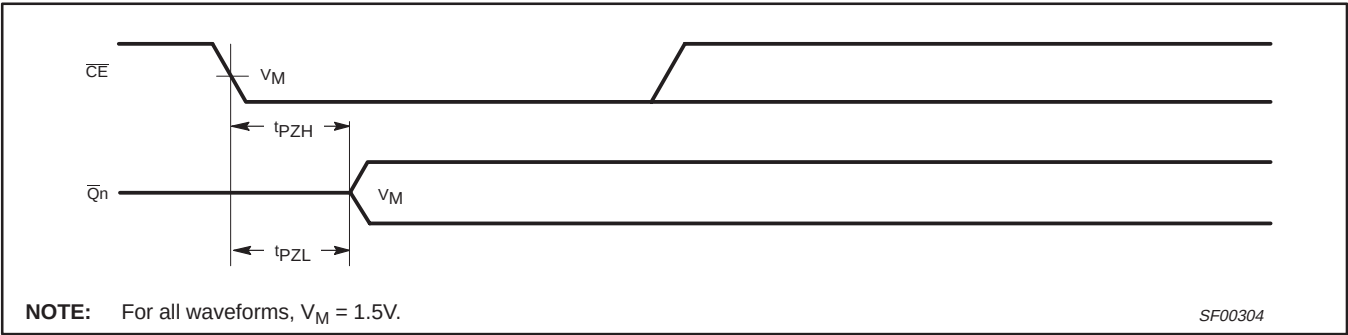
AC WAVEFORMS FOR READ CYCLES



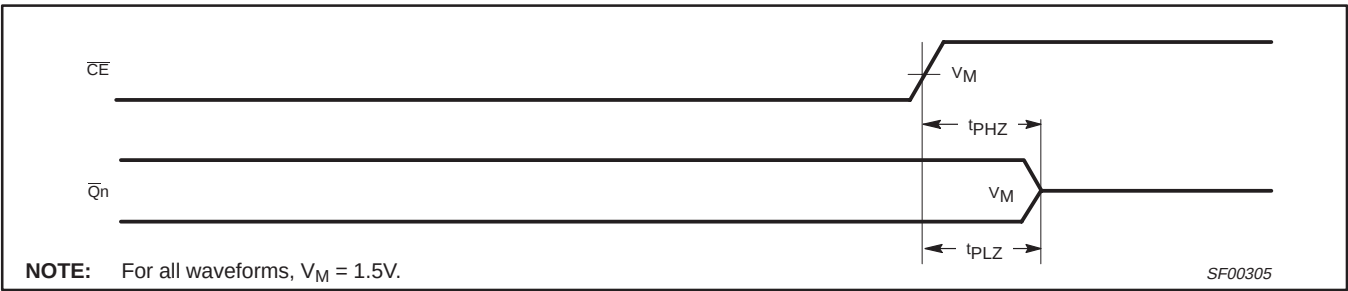
Waveform 1. Read cycle, address access time

64-bit TTL bipolar RAM, inverting (3-State)

74F189A

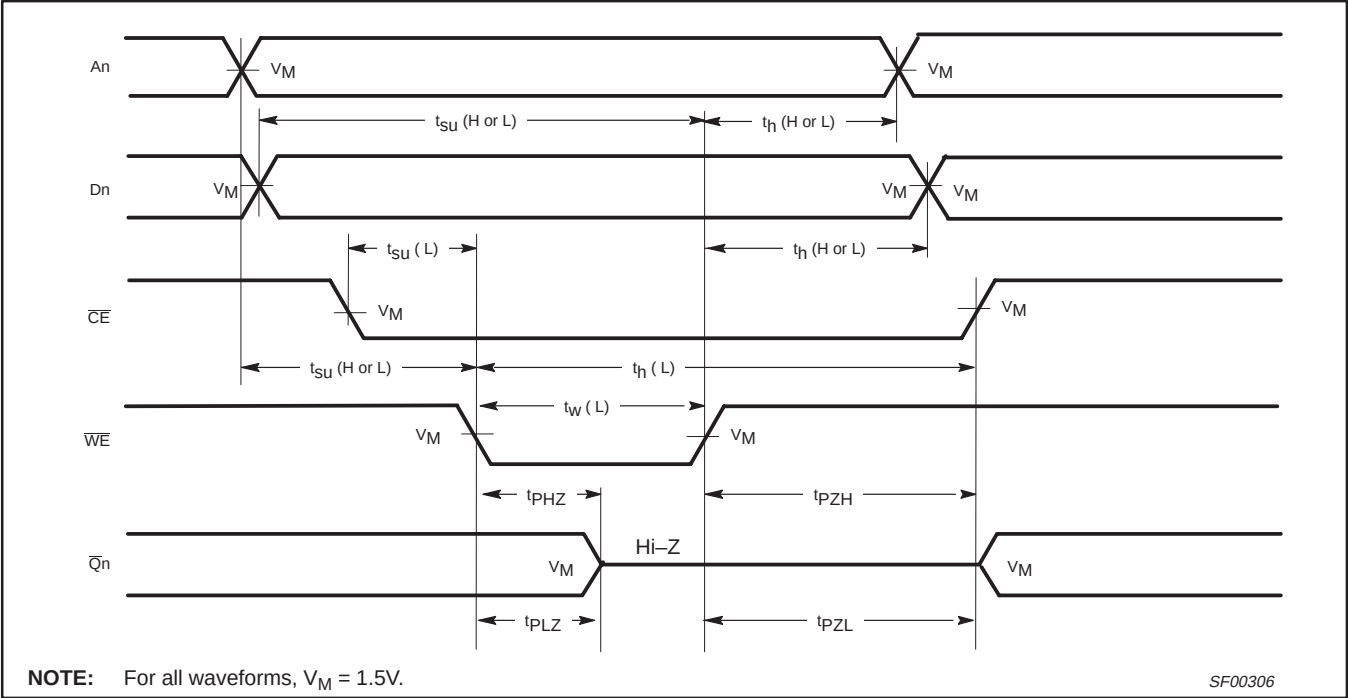


Waveform 2. Read cycle, chip enable access time



Waveform 3. Read cycle, chip disable time

AC WAVEFORMS FOR WRITE CYCLE

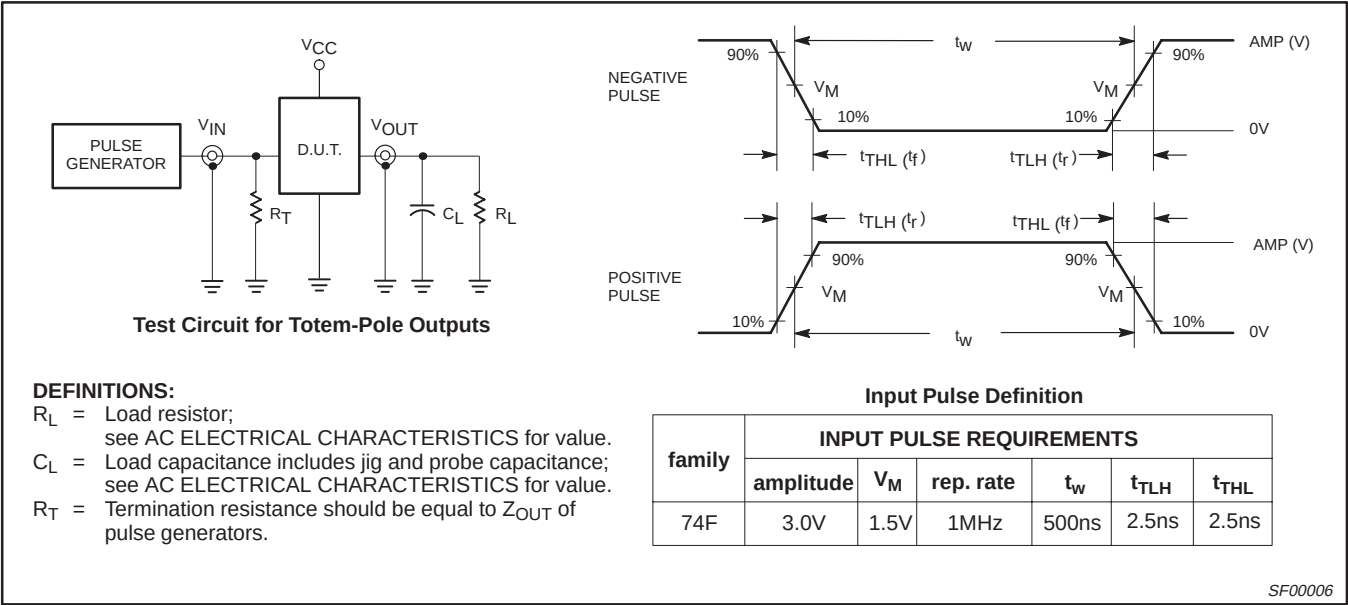


Waveform 4. Write cycle

64-bit TTL bipolar RAM, inverting (3-State)

74F189A

TEST CIRCUIT AND WAVEFORM

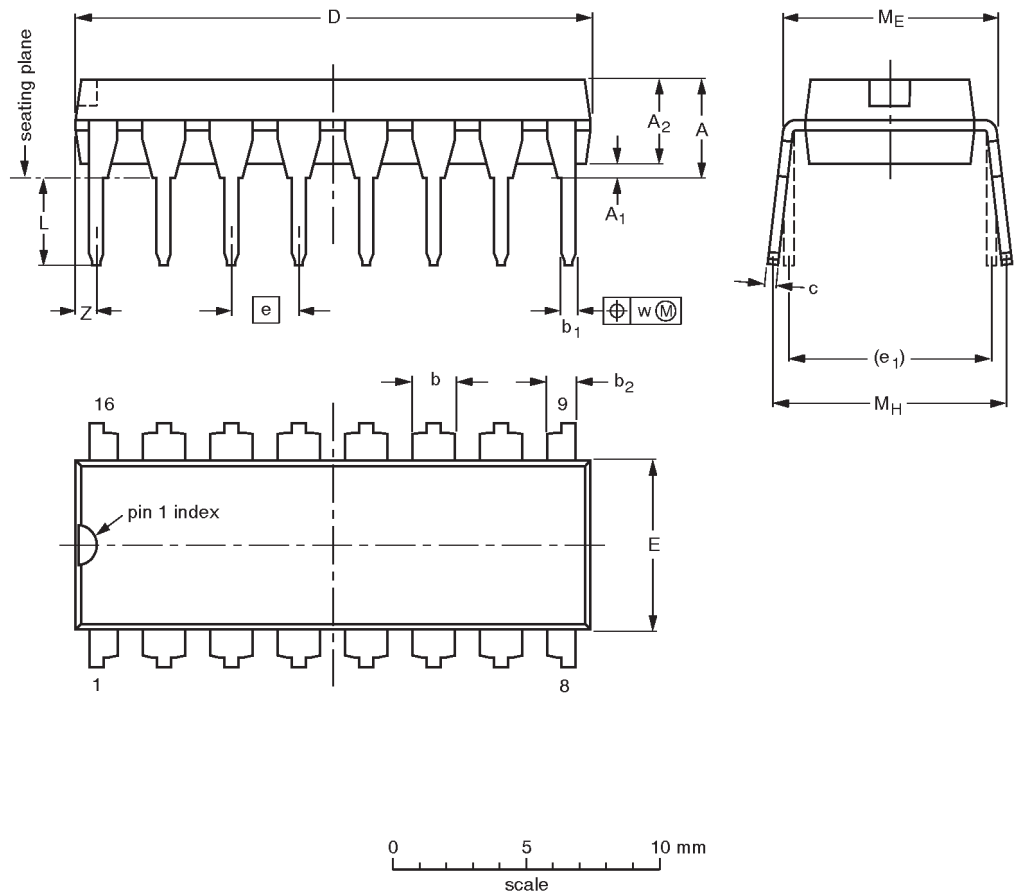


64-bit TTL bipolar RAM, inverting (3-State)

74F189A

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	b ₂	c	D ⁽¹⁾	E ⁽¹⁾	e	e ₁	L	M _E	M _H	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	1.25 0.85	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	0.76
inches	0.17	0.020	0.13	0.068 0.051	0.021 0.015	0.049 0.033	0.014 0.009	0.77 0.73	0.26 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.030

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

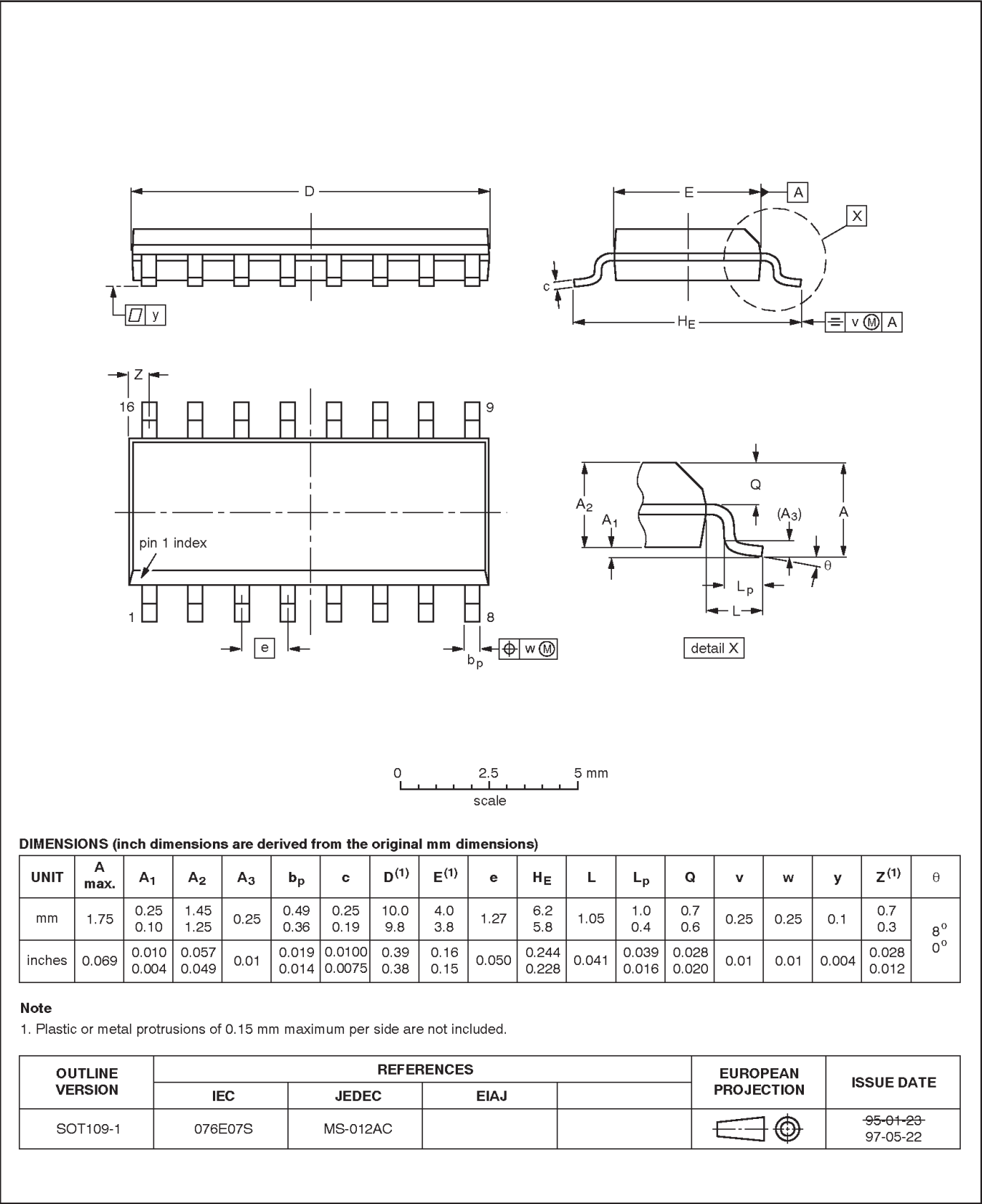
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT38-4						92-11-17 95-01-14

64-bit TTL bipolar RAM, inverting (3-State)

74F189A

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



64-bit TTL bipolar RAM, inverting (3-State)

74F189A

Data sheet status

Data sheet status	Product status	Definition [1]
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.

[1] Please consult the most recently issued datasheet before initiating or completing a design.

Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Disclaimers

Life support — These products are not designed for use in life support appliances, devices or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips Semiconductors customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors for any damages resulting from such application.

Right to make changes — Philips Semiconductors reserves the right to make changes, without notice, in the products, including circuits, standard cells, and/or software, described or contained herein in order to improve design and/or performance. Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no license or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified.

Philips Semiconductors
811 East Arques Avenue
P.O. Box 3409
Sunnyvale, California 94088-3409
Telephone 800-234-7381

© Copyright Philips Electronics North America Corporation 1998
All rights reserved. Printed in U.S.A.

print code

Date of release: 10-98

Document order number:

9397-750-05092

Let's make things better.